Characterization of amorphous and nanocrystalline carbon films

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Abstract

Amorphous and nanocrystalline carbon films possess special chemical and physical properties such as high chemical inertness, diamond-like properties, and favorable tribological properties. The materials usually consist of graphite and diamond microstructures and thus possess properties that lie between the two. Amorphous and nanocrystalline carbon films can exist in different kinds of matrices and are usually doped with a large amount of hydrogen. Thus, carbon films can be classified as polymer-like, diamond-like, or graphite-like based on the main binding framework. In order to characterize the structure, either direct bonding characterization methods or the indirect bonding characterization methods are employed. Examples of techniques utilized to identify the chemical bonds and microstructure of amorphous and nanocrystalline carbon films include optical characterization methods such as Raman spectroscopy, Ultra-violet (UV) Raman spectroscopy, and infrared spectroscopy, electron spectroscopic and microscopic methods such as scanning electron microscopy (SEM), X-ray photoelectron spectroscopy (XPS), Auger electron spectroscopy, transmission electron microscopy, and electron energy loss spectroscopy, surface morphology characterization techniques such as scanning probe microscopy (SPM) as well as other characterization methods such as X-ray reflectivity and nuclear magnetic resonance. In this review, the structures of various types of amorphous carbon films and common characterization techniques are described.

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1. Introduction

There has been a lot of interest on amorphous and nanocrystalline carbon films in the past twenty years because they exhibit beneficial chemical and physical properties such as high chemical inertness, diamond-like properties [1–5], and favorable tribological properties [6,7] suitable for industrial use. Their unique properties can be attributed to the special and interesting properties of the microstructures. The materials usually comprise a hybrid of graphite and diamond microstructures and thus possess properties that lie between the two. Amorphous and nanocrystalline carbon films can exist in different kinds of matrices and are usually doped with a large amount of hydrogen thereby making the materials even more diverse. The most common chemical bonds in amorphous and nanocrystalline carbon are sp\(^3\) and sp\(^2\) hybridizations. In the sp\(^3\) configuration, a carbon atom forms four sp\(^3\) orbitals making a strong \(\sigma\) bond to the adjacent atom. In some of the carbon films with high hardness, the sp\(^3\) content is sometimes in excess of 80% [8–15]. These films are commonly referred to as tetrahedral amorphous carbon or ta-C films. In these films, sp\(^3\) dominates to establish a diamond-like base framework. In the sp\(^2\) configuration, a carbon atom forms three sp\(^2\) orbitals forming three \(\sigma\) bonds and the remaining \(p\) orbital forms a \(\pi\) bond. The \(\pi\) orbital geometrically lies normal to the \(\sigma\) bond plane and is the weaker bond so that it is closer to the Fermi level, \(E_f\). The three \(\sigma\) bonds and \(\pi\) bond usually constitute a ring plane in sp\(^2\) clusters. A variety of larger clusters can be formed by fusing double bonds and rings [16]. Under the constraint of the rigid sp\(^3\) network, the rings can coexist with each other or may be deformed. Robertson and O’Reilly have suggested a model [16] for amorphous carbon that consists of sp\(^2\)-bonded clusters interconnected by a random network of sp\(^3\)-bonded atomic sites. Taking advantage of extensive characterization...
and research, the structure and properties of carbon films have become more understood. Several other structural models have also been proposed, such as the one based on three dimensional all-sp$^2$ bonding introduced by Côté et al. [17] and Liu et al. [18,19]. In their model, they propose an all-sp$^2$ structure that can yield a high bulk modulus and low bulk modules as determined by their bond lengths. Experimental results have confirmed the possibility of the film structure to be composed of a matrix of dispersed cross-linked sp$^2$ sites that provide the network with rigidity [20–22]. In addition to sp$^2$ and sp$^3$, there is some evidence of the presence of sp bonds as well [23]. In the sp configuration, a carbon atom forms two sp orbitals thus two σ bonds and the other valence electrons constitute two perpendicular π orbitals.

Amorphous and nanocrystalline carbon films can exist in threefold (sp$^2$ bonding) and fourfold (sp$^3$ bonding) coordination, and unlike its crystalline counterpart, they may consist of any mixture of the two bonding types [13]. At the beginning, it was generally believed that the high hardness arises from the sp$^2$ rigid framework, but recent studies have indicated that sp$^3$ bonds can also render carbon films with relatively high hardness. Though the sp$^3$ and sp$^2$ bonds do not show the same long distance order characteristics as they do in crystalline diamond or graphite, the bonds sometimes can intermix and exhibit extended order on a nano scale. When the sizes of sp$^2$ and sp$^3$ clusters become large enough, nanocrystalline graphite and diamond structures can be observed. They have been detected not only in as-deposited carbon films (usually prepared under a high temperature) [24–26] but also after annealing, mechanical rubbing in friction tests, or even irradiation [27–29].

In amorphous carbon and nanocrystalline carbon films, doped hydrogen usually plays an important role. Recent studies have revealed experimental evidence of the existence of transpolyacetylene (TPA) chains in a-C:H films free of nano crystalline diamond [30]. In a related study, it was found that a considerable amount of hydrogen (up to ≈60 at.%) could be incorporated in the films leading to soft polymer-like amorphous carbon (PLC) [31]. The hydrogenated carbon films are characterized by a wide optical band gap and they can exhibit special optical absorption, intense photoluminescence, and electron affinity. The synthesis, properties, and thermal stability of hydrogenated carbon films have aroused enormous research interest due to their potential applications [31–36]. Though the only bond for hydrogen in carbon films is C-H, various combinations of the C-H bond make characterization quite difficult and complicated. It has been proposed that in carbon films either in the amorphous state or nanocrystalline state, there are variable-sized and complicated polyacetylene and/or olefinic chains and/or aromatic clusters [16,30]. Above all, though amorphous and nanocrystalline carbon films commonly only consist of carbon and hydrogen, they are interconnected in many ways to yield materials with distinctly different properties. Carbon films can be classified as polymer-like, diamond-like, or graphite-like based on the main binding framework [31]. In order to characterize the structure, either direct bonding characterization methods or the indirect bonding characterization methods are employed. Examples of techniques utilized to identify the chemical bonds and microstructure of amorphous and nanocrystalline carbon films include optical characterization methods such as Raman spectroscopy, UV Raman spectroscopy, and infrared spectroscopy, electron spectroscopic and microscopic methods such as scanning electron microscopy (SEM), X-ray photoelectron spectroscopy (XPS), Auger electron spectroscopy, transmission electron microscopy, and electron energy loss spectroscopy, surface morphology characterization techniques such as scanning probe microscopy (SPM) as well as other characterization methods such as X-ray reflectivity and nuclear magnetic resonance.

It should be noted that though previous studies have verified the presence of both sp$^2$ and sp$^3$ bonds and the lack of long-range order, short order in such films has not been directly observed due to the lack of techniques with sufficient resolution and sensitivity to the atomic structure in the thin films [23]. In addition, the use of multiple characterization techniques is preferred as comparison can better disclose the detailed structures of the films. In this paper, techniques that are commonly employed to study carbon films are described.

2. Optical characterization methods

2.1. Raman spectroscopy

Raman spectroscopy is a popular nondestructive, ambient probing tool to characterize the structure and usually imposes very little constraint on the substrate size [37–43]. When a light quantum hν hits a surface, an elastic scattering process, that is, Rayleigh scattering of quanta with energy hν ensues. This process has the highest probability. However, there also exists an inelastic process in which the vibrational energy is altered by hv. The inelastic process is called Raman scattering and quanta of energy hv + hv are emitted. Because vibration of the atoms in the excited state is much less than that of the ground state atoms at ambient temperature according to Boltzmann’s law, it is more efficient to excite ground-state atoms to a vibrationally excited state than to receive the decay energy from the vibrating atoms. Hence, the emitted quanta having energy of hv = hv can be more prevalent than the emitted quanta with energy of hv + hv. The Raman lines corresponding to the quanta with energy of hv − hv are referred to as the Stokes lines whereas the higher energy lines (hv + hv) are called the anti-Stokes lines. As the intensities of the anti-Stokes lines are lower, only the Stokes lines are usually recorded in the Raman spectrum [44,45]. The light scattering process is illustrated in Fig. 1 [44].

Raman spectroscopy is a very effective way to investigate the detailed bonding structure of carbon films. Though there is still debate on the exact relationship between the atom vibration and Raman spectra, the method is the most widely
Fig. 1. Schematic diagram of the principle of Raman scattering [44]: (a) inelastic scattering of an optical quantum hitting the materials; (b) term diagram; (c) Raman spectra. Because vibration of atoms in the excited state is much less than that of the ground state atoms, the Stokes line is stronger than anti-Stokes line. A Raman peak composed of the D and G components is one of the most widely investigated attributes in amorphous carbon films. In graphite nanocrystalline carbon films, the D peak usually stands out and the width is smaller (only...
the high temperature annealed nanographite film is shown in Fig. 2). As shown in Fig. 2, the first peak is a sharp one at 1332 cm$^{-1}$ with the typical shouldered amorphous carbon peak as the background, and the other one has four separate peaks located at around 1150 cm$^{-1}$, 1350 cm$^{-1}$, 1500 cm$^{-1}$, and 1580 cm$^{-1}$. The peak at around 1150 cm$^{-1}$ is assigned to the nanocrystalline phase of diamond, 1500 cm$^{-1}$ to disordered sp$^3$ carbon, and 1350 cm$^{-1}$ and 1580 cm$^{-1}$ to the popularly known D and G bands. The Raman spectrum of glassy carbon films resembles that of commercial graphite.

![Raman spectra](image)

Fig. 2. Typical Raman spectra acquired from different kinds of carbon films (our data plus refs. [48,53,54,67]).
but the intensity of D and G peaks is very different. Fig. 2 only displays schematically the Raman spectra expected from different kinds of amorphous carbon films. In order to obtain more details, more data analysis is necessary.

2.1.2. Peak fitting

To reveal more information about the structure of the carbon films, the Raman spectra should be deconvoluted. However, owing to the myriad of combinations of the carbon and carbon–hydrogen structures in the materials, fitting of the Raman spectra is not an easy task and requires different processes.

The most common Raman spectra fitting method is to employ two Gaussian peaks with linear background or non-linear background subtraction [46,68,69] with the G peak centered at 1360 cm\(^{-1}\) and the D peak at around 1580 cm\(^{-1}\). It is based on the assumption that the amorphous carbon films are composed of disordered sp\(^2\) and sp\(^3\) networks. The fitted peak intensity of D and G is used to evaluate \(I_0\) that reflects the in-plane crystallite size. The second spectra fitting method proposed by Prawer et al. [70] utilizes a Breit–Winger–Fano (BWF) line shape and linear background subtraction methods. The BWF line shape is described by:

\[
I(\omega) = I_0 \left[ \frac{1}{1 + \left[2(\omega - \omega_0)/\Gamma \right]^2} \right]^{1+Q} 
\]

where \(I(\omega)\) is the intensity as a function of frequency, \(I_0\) the maximum peak intensity, \(\omega_0\) and \(\Gamma\) the peak position and full width at half-maximum (FWHM), respectively, and \(Q\) is the
BWF coupling coefficient. In the limit that 1/Q approaches zero, the Lorentzian line shape is acquired. Thus, a total of six parameters are required to fit the data, namely \( k_0, m_0, Q, \Gamma \) and two parameters for the linear background. Employing this fitting method, the additional D peak is usually submerged. This is possible since there is no independent species, for instance, well-isolated sp\(^2\) and sp\(^3\) domains in the films [70–73]. Apart from the G and D peaks, some other peaks can be observed occasionally [74], and to obtain a better fit, additional peaks are usually introduced [75–78], for example, in polymeric amorphous carbon films or films with adventitious elements such as O, F or N [76–78].

It should be noted that based on the discovery that the 1100 cm\(^{-1}\) UV Raman peak may reveal information pertaining to sp\(^3\) bonding, visible Raman peaks should also be used to probe sp\(^3\) bonding. Chen et al. [79] used their results and theoretical analysis and experimental results from others [80–82] to conclude that two peaks at around 1168 cm\(^{-1}\) and 1271 cm\(^{-1}\) are associated with sp\(^3\) diamond bonding in ta-C films. Hence, the Raman spectra contain composite information that must be deconvoluted by careful curve fitting.

2.1.3. Peak position and width

Though the origin of both the D and G bands is not well understood [20,43,70,83], the position and width of these two peaks are usually used as a reference to determine the deposition parameters, film properties as well as structure. The overall spectrum is characteristic of each type of carbon but a single-wavelength Raman spectrum may be indistinguishable [37]. Fig. 3(a) shows the density of a-C:H, a-C (film formed roughly at 10 eV), and i-C (hydrogen-free film formed at 50–200 eV) films as a function of the G line width and Fig. 3(b) reveals the position of Raman G line as a function of the substrate bias for a-C:H films [43].

It should be mentioned that even for the same sample, the Raman peak position and width vary with the laser excitation wavelength. Fig. 4 depicts the variation of dispersion of the G peak using different excitation wavelengths. The G peak disperses in more disordered carbon and the dispersion is proportional to the degree of disorder, but it does not disperse in graphite, glassy carbon, or nano crystalline graphite [37]. The FWHM of the peak decreases with increasing excitation energy because of the gap variation of the carbon films. A
higher excitation energy can excite a wider gap at the same wavenumber. That is to say, to excite the same gap, a smaller packet of wavenumber is needed for higher energy photons, thus resulting in a smaller width. The width of the peak also increases due to the site-to-site variation in the number of next nearest neighbors, that is, when sp² C atoms have sp³ C neighbors.

2.1.4. \( I_D/I_G \)

The \( I_D/I_G \) ratio (intensity of the D peak to that of the G peak) is known to vary in DLC films synthesized by different methods and parameters and sometimes even for films fabricated by the same method. It is believed that \( I_D/I_G \) is related to the size of the graphite planes in the DLC films, and this has been used to analyze the thermal stability and frictional properties of the materials. The D peak intensity is usually increased after annealing at above 300 °C or after a long friction test. This phenomenon is generally ascribed to the conversion of sp³ bonds to sp² bonds, desorption of hydrogen, and conversion of carbon structure to nanocrystalline graphite.

The use of \( I_D/I_G \) to evaluate the size of the graphite cluster in the study of properties such as the degree of disorder in amorphous carbon, nano graphite crystal size, and the domain for glassy carbon films. However, direct correlation is not as straightforward when the \( I_D/I_G \) value is larger than the maximum value observed in the microcrystalline graphite studies. For instance, Cho et al. have observed that when the value is over 1.1, the linear relationship between \( I_D/I_G \) and the inverse of the microcrystallite size \( 1/L_a \) may no longer hold. They ascribe the increase in the \( I_D/I_G \) ratio to the increase in the number of graphite microcrystallites with less defects in lieu of the increase in \( L_a \). This also explains the increase in the intensity of D band for most amorphous films after annealing at a higher temperature.

2.2. UV Raman

The success of conventional visible Raman spectroscopy to differentiate different types of amorphous carbon films has led to the development of Raman excitation using ultraviolet light. This technique is a powerful method to characterize the carbon film structures and is considered to be a future method to characterize amorphous and nanocrystalline carbon films especially with respect to sp³ C atoms. The advantage of UV Raman is its higher excitation energy than visible Raman. The Raman intensity from sp³ C can be increased while previously dominant resonance Raman scattering from sp² C atoms is suppressed. Since the overall Raman intensity is proportional to \( \sigma^2 \), where \( \sigma \) is the frequency of incident photons, UV excitation is more advantageous considering the weak Raman signal from thin DLC films. Hence, UV Raman spectroscopy is the preferred technique to probe the surface structure because UV only excites the topmost \( \sim 10-15 \) nm of the sample surface at 224 nm. For lower excitation energies, the probed depth is larger.

Gilkes et al. and Merkulov et al. have proposed that if there are sp³ structures in the carbon films, there will be UV excitation at around 1060–1100 cm\(^{-1}\) due to the C–C sp³ vibration. This transition only manifests under UV irradiation. Fig. 5 displays the UV Raman spectra of sputtered a-C films with different sp³ contents from 6% to 75% based on the results of Merkulov et al. The intermediate frequency peak at 1150 cm\(^{-1}\) is assigned to sp³ C excitation with some sp² contributions. It is observed that:

1. one intermediate frequency peak at \( \sim 1180 \) cm\(^{-1}\) appears in the UV Raman spectra of the diamond like amorphous carbon films;
2. the G peak shifts from \( \sim 1580 \) cm\(^{-1}\) to \( \sim 1620 \) cm\(^{-1}\) as the fraction of sp³ C increases from \( \sim 6 \) at.% to \( \sim 75 \) at.%;
3. the peak widths also increase with higher sp³ fraction.

Using peak fitting, it is found that sp³ C contributions to the peak at 1150 cm\(^{-1}\) have a striking resemblance to the theoretical phonon density of state (PDOS) of the sp³ net-
work calculated by Wang and Ho [80]. A conclusion can thus be drawn that the peak shift and widening are due to the site-to-site variation in the number of the sp2 C and sp3 C neighbors.

Consistent with those observed by Merkulov, Gilkes’s results reveal an additional peak, width increase, and shift to higher wavenumber of the G peak. It is also found that the peak at 1100 cm$^{-1}$ is close to a main peak as suggested by the vibrational density of states (VDOS) calculated by Beeman et al. [81] for a fully sp3-bonded continuous random network. They attribute the shift in the G peak to a larger contribution from olefinic (chain) sp2 groups.

It should be noted that in UV Raman, the sensitivity for the sp2 Raman vibrations is still stronger than that of the sp3 by a factor of 5–10 [12]. Hence, in the analysis of carbon films by UV Raman vibration, the sp2 peak excitation can still dominate. It is thus too early to draw the conclusion that UV Raman is the most powerful method to determine the sp3 fraction from any kind of carbon films because there has been relatively little literature on this topic.

2.3. Infrared spectroscopy

Infrared spectroscopy is about 100 years old whereas Raman spectroscopy is more than 70. Although the excitation mechanism is somewhat similar, infrared and Raman spectroscopies have evolved separately. While infrared spectroscopy has quickly become the workhorse of vibrational spectroscopy in the industry and analytical laboratories, Raman spectroscopy has hitherto been limited to research activities primarily [44]. Infrared spectra are usually recorded by measuring the transmittance of light quanta. The frequencies of the absorption bands are proportional to the energy difference between the vibrational ground and excited states as illustrated in Fig. 6. The absorption bands due to the vibrational transitions are found in the wavenumber region of $\nu=4000–10$ cm$^{-1}$ [44].

Amorphous carbon films consist of different percentages of sp2, sp3 and even sp1 carbon atoms and hydrogen atoms are commonly incorporated into the carbon network. Owing to the localized nature of C–H vibrations and the sensitivity of their frequency to the nature of the C=C bonds, the analysis of the C–H vibrational modes using infrared spectroscopy can be used to characterize the amorphous carbon films, especially for hydrogenated carbon films [47,101]. The first assignments of vibrational frequencies to distinguish C–H modes were made by Dischler et al. [102,103]. The IR absorption spectrum consists of C–H stretching modes at 2800–3300 cm$^{-1}$ and C–C modes and C–H bending modes below 2000 cm$^{-1}$ are exhibited in Fig. 7 [102]. Dischler published a complete list of all possible C–H vibrations (10 stretching, 17 bending, and 1 torsion) for polymeric and diamond-like amorphous carbon [104]. Summarizing the results of Dischler [104] and Heitz et al. [105], Robertson formulated the assignments of the various modes in a-C:H, as shown in Table 1.

Aside from qualitative characterization the spx–CHy types, efforts have been made to quantitatively determine the sp2/sp3 ratio, analyze the C–H vibrations in terms of their absorption strength, and derive the total amount of H atoms [101,105–110]. However, accurate quantitative determination of the amorphous composition by these methods is difficult because a model of amorphous carbon film structure is quite complicated and has not been conclusively derived. In addition, the IR spectra acquired from the films tend to be a composite of many different vibrations of C–H bonds.

Another common utility of IR spectra is to examine the optical gap of the carbon film. The optical gap of the amorphous film can be assessed using IR transmission and reflection measurements [102,111–113]. By extrapolation using the following relation (Tauc relation), the abscissa can yield the optical gap $E_{opt}$ [102,113,114].

$$ (\alpha E)^{1/2} = G(E - E_{opt}) $$

where $E$ is phonon energy ($h\nu$), $G$ is the gradient of line; $E$ is the photon energy, $\alpha$ is the coefficient. In addition,

$$ T = (1 - R)^2 \exp(-2\alpha d) $$

where $T$ is transmittance.
Table 1
Assignments of IR vibrational frequencies in a-C:H [47]

<table>
<thead>
<tr>
<th>Wavenumber (cm⁻¹)</th>
<th>Configuration</th>
<th>Olefinic or aromatic</th>
<th>Symmetrical or asymmetrical</th>
</tr>
</thead>
<tbody>
<tr>
<td>3090</td>
<td>sp² CH</td>
<td>Olefinic</td>
<td>A</td>
</tr>
<tr>
<td>3070</td>
<td>sp² CH</td>
<td>Olefinic</td>
<td>A</td>
</tr>
<tr>
<td>2960–3000</td>
<td>sp² CH</td>
<td>Olefinic</td>
<td>S</td>
</tr>
<tr>
<td>2975</td>
<td>sp² CH</td>
<td>Olefinic</td>
<td>S</td>
</tr>
<tr>
<td>2955</td>
<td>sp² CH</td>
<td>Olefinic</td>
<td>A</td>
</tr>
<tr>
<td>2900</td>
<td>sp¹ CH</td>
<td>Olefinic</td>
<td>S</td>
</tr>
<tr>
<td>2880</td>
<td>sp² CH</td>
<td>Olefinic</td>
<td>S</td>
</tr>
<tr>
<td>2853</td>
<td>sp² CH</td>
<td>Olefinic</td>
<td>S</td>
</tr>
<tr>
<td>2440</td>
<td>sp¹ CH</td>
<td>Olefinic</td>
<td>S</td>
</tr>
<tr>
<td>1410</td>
<td>sp³ CH</td>
<td>Aromatic</td>
<td>A</td>
</tr>
<tr>
<td>1400</td>
<td>sp² CH</td>
<td>Aromatic</td>
<td>A</td>
</tr>
<tr>
<td>1390</td>
<td>sp¹ CH</td>
<td>Aromatic</td>
<td>S</td>
</tr>
<tr>
<td>1380</td>
<td>sp² (CH₃)</td>
<td>Aromatic</td>
<td>S</td>
</tr>
<tr>
<td>1375</td>
<td>sp² CH</td>
<td>Aromatic</td>
<td>S</td>
</tr>
<tr>
<td>1130</td>
<td>sp² CH₂</td>
<td>Aromatic</td>
<td>S</td>
</tr>
<tr>
<td>1190</td>
<td>sp² (CH₃)</td>
<td>Aromatic</td>
<td>S</td>
</tr>
<tr>
<td>1065</td>
<td>sp² CH₂</td>
<td>Aromatic</td>
<td>S</td>
</tr>
<tr>
<td>1020</td>
<td>sp² CH₂</td>
<td>Aromatic</td>
<td>S</td>
</tr>
<tr>
<td>950</td>
<td>sp² CH₂</td>
<td>Aromatic</td>
<td>S</td>
</tr>
<tr>
<td>920</td>
<td>sp² CH₂</td>
<td>Aromatic</td>
<td>S</td>
</tr>
<tr>
<td>865</td>
<td>sp² CH₂</td>
<td>Aromatic</td>
<td>S</td>
</tr>
<tr>
<td>840</td>
<td>sp² CH₂</td>
<td>Aromatic</td>
<td>S</td>
</tr>
</tbody>
</table>

where T and R are, respectively, the transmission and reflection coefficients measured in the photon energy range between 2 and 6 eV, and d is the film thickness. It should be noted that the optical gap can also be defined as the energy at which the optical absorption coefficient reaches 10⁴ cm⁻¹ [111,115,116].

### 3. Electron spectroscopy and microscopy

#### 3.1. X-ray photoelectron spectroscopy (XPS)

When the surface is irradiated with X-rays, electron emission results due to the photoelectric and Auger effects. The photoelectron emission process is illustrated in Fig. 8. The kinetic energy of the emitted photoelectrons is given by [117]:

$$E_k = h\nu - E_b - W_s$$

where \(h\nu\) is the energy of the photon, \(E_b\) the binding energy of the atomic orbital from which the electron originates, and \(W_s\) is the spectrometer work function. The technique is called X-ray photoelectron spectroscopy (XPS) and also referred to as electron spectroscopy for chemical analysis (ESCA) in older literature. Because each element has a unique set of binding energies, XPS can be used to identify and determine the concentration of the elements within the escape depth of the photoelectrons in the near surface region. Variations in the elemental binding energies (the chemical shifts) arise from the differences in the chemical potential and polarizability of the compounds. These chemical shifts can be used to identify the chemical state of the materials [117].

Compared with optical analysis methods, XPS is not as frequently used in the analysis of carbon films since it cannot detect hydrogen. However, because it can reveal the binding energy of the carbon atoms and discern the hybrid sp³ and sp² bonds, it is a very powerful method to evaluate the structure of amorphous carbon films without causing excessive damage to the materials [118–127]. Furthermore, because of the lack of direct binding energy information from optical characterization methods, XPS is complementary to optical characterization methods [119,128]. Owing to its high sensitivity to chemical shifts or the chemical environment of the probed atom, it is a very useful tool to characterize the structures of the doped amorphous carbon films [125,129–132].

The Cls peak position in diamond is 285.50 eV that is about 1.35 eV higher than that in graphite (284.15 eV) [133]. The ionization cross-sections in the core levels are exclusively dependent on the atomic factors. The intensity of the core-level peaks is then directly proportional to the density of atoms [118]. If the Cls core-level binding energies of the sp³ and sp² hybrids in a-C are different, as in graphite [134] and diamond [135], the Cls peak position will vary and can be deconvoluted into two subpeaks, and so proper peak fitting can reveal the sp³ to sp² ratio. Fig. 9 shows the Cls spectra acquired from amorphous carbon films deposited using different vacuum arc deposition parameters shown in Table 2 [119]. The shift of the peak position is obvious. By comparing with the Raman shift result, Li et al. have drawn a conclusion that XPS is very useful in supplementing the optical characterization (Raman) of amorphous carbon films [119].

As aforementioned, XPS is a useful method to assess the sp³ and sp² components. It should be noted that it is not necessary to use reference samples since the chemical shifts of the Cls photoelectron spectra due to sp³ and sp² do not bear a direct relationship with the matrix [118]. The intensity of the binding energy is linearly proportional to the fraction of sp³ and sp² bonds and the ionization cross sections are independent of the chemical state of the atoms for X-ray photons with energies well above the ionization threshold [120,136]. Diaz et al. [118] proposed a sp³ and sp² identification method...
Table 2

<table>
<thead>
<tr>
<th>Sample</th>
<th>Focusing coils current (A)</th>
<th>Filter coils current (mA)</th>
<th>Arc current (A)</th>
<th>Arc voltage (V)</th>
<th>Gases (SCCM)</th>
<th>Working vacuum (Pa)</th>
<th>Bias current (mA)</th>
<th>Deposition time (min)</th>
</tr>
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<tbody>
<tr>
<td>1</td>
<td>6/2</td>
<td>–</td>
<td>78</td>
<td>40–52</td>
<td>Ar:130</td>
<td>3.4 × 10⁻²</td>
<td>0</td>
<td>4</td>
</tr>
<tr>
<td>2</td>
<td>7/3</td>
<td>–</td>
<td>100</td>
<td>25–30</td>
<td>Ar:40</td>
<td>6 × 10⁻²</td>
<td>100</td>
<td>3</td>
</tr>
<tr>
<td>3</td>
<td>7/3</td>
<td>–</td>
<td>66</td>
<td>20–30</td>
<td>Ar:60</td>
<td>6.4–7 × 10⁻²</td>
<td>150</td>
<td>1</td>
</tr>
<tr>
<td>4</td>
<td>7/2.5</td>
<td>–</td>
<td>82</td>
<td>20–30</td>
<td>Ar:70; C₂H₂:40</td>
<td>7 × 10⁻⁴</td>
<td>1000</td>
<td>5</td>
</tr>
<tr>
<td>5</td>
<td>7/2.5</td>
<td>–</td>
<td>82</td>
<td>20–32</td>
<td>Ar:70</td>
<td>7 × 10⁻⁴</td>
<td>1000</td>
<td>10</td>
</tr>
<tr>
<td>6</td>
<td>5/2</td>
<td>220</td>
<td>50</td>
<td>30–32</td>
<td>Ar:40</td>
<td>8 × 10⁻²</td>
<td>150</td>
<td>20</td>
</tr>
<tr>
<td>7</td>
<td>5/2</td>
<td>220</td>
<td>50</td>
<td>30–32</td>
<td>Ar:126</td>
<td>5 × 10⁻²</td>
<td>600</td>
<td>20</td>
</tr>
</tbody>
</table>

by assuming a higher binding energy due to sp³ hybrids and the higher binding energy of the C1s core level in diamond [137] than in graphite [134,135].

In order to deconvolute the C1s spectra, the diamond surface and bulk C1s spectra decomposition method proposed by Morar et al. [135] can be used. In this method, the measured spectra are first fitted by using a Lorentzian-shaped peak to represent the broadened C1s level. The Lorentzian peak is convoluted with a Gaussian-shaped broadening function and added to a modeled background. The Gaussian represents broadening resulting from variations in the position of the Fermi level within the band gap as well as any vibrational broadening. The modeled background includes an intrinsic secondary electron component with a contribution proportional to the integral under the photoemission peak and an extrinsic secondary electron component that is not directly associated with the C1s photoemission process.

By subtracting the background, Diaz decomposed the C1s spectra peak using five variable parameters: Gaussian width, binding energies of sp³ and sp², and the singularity index for the sp² component. In the calculation performed by Haerle et al. [120], four additional parameters are added: intensities of the two components plus two used for defining a Shirley background proportional to the integrated peak intensity. For the sp² component, the Doniac–Sunjic function is usually used [118,120,138]. In this process, convolution of a Gaussian and a Lorentzian with an additional parameter allowing for asymmetry in the line shape is employed. This function is used to account for the asymmetric line shapes resulting from the screening due to electron-hole pair excitations at the Fermi energy.

Because some of the amorphous carbon films have poor conductance, special care should be exercised to avoid sample surface charging during the XPS analysis. The success can be judged by showing that the peak position is independent of the intensity of the incident X-rays.

3.2. Auger electron spectroscopy (AES)

Auger electron emission is initiated by the creation of an ion with an inner shell vacancy induced by bombardment of electrons, X-rays, or ions. Electron beam excitation is most common due to the ability to focus an electron beam onto a small area for microanalysis, as illustrated in Fig. 10. The kinetic energy of an Auger electron is equal to the energy difference of the singly ionized state and the double ionized final state. For an arbitrary ABC transition in an atom of atomic number , the Auger electron kinetic energy is given by the difference in the binding energies of energy levels A, B and C [139]:

\[ E_{ABC}(z) = E_A(z) - E_B(z) - E'_C(z) - W_s \] (6)

where \( W_s \) is the spectrometer work function and \( E'_C \) is the binding energy of a level in the presence of a core hole and is greater than the binding energy of the same level in a neutral atom. Auger transitions are typically designated by the energy of the electrons involved using X-ray spectroscopy nomenclature. The first label corresponds to the energy level of the initial core hole, whereas the second and third terms refer to the initial energy levels of the two electrons involved in the Auger transition. AES is usually used to determine the
elemental composition and in some cases also the chemical state of the atoms in the surface region of a solid material [139]. Coupled with scanning capabilities, AES can be used to map the distribution of the elements in the near surface region within the escape depth of the Auger electron. Compositional depth profiles can also be obtained by performing ion sputtering in concert with AES.

AES can be used to characterize amorphous carbon films [121,140-148], although it is not as common as other non-destructive techniques. Mizokawa et al. [149] have confirmed that high-energy electron bombardment can affect the surface structure of the carbon films. After long time electron irradiation, the AES spectra from DLC films resemble that of soft amorphous carbon [149,144]. While X-ray excited Auger electron spectra (XAES) can be used to study the amorphous carbon films structures and be used as a fingerprint of the carbon state and the characterization of diamond-like carbon films [149,141,145], it does not mean that electron excited AES cannot be used. In fact, AES has been used to characterize the chemical states of the carbon films [150] and to derive the $sp^2/sp^3$ ratio [122], provided that electron beam damage is understood.

3.3. Transmission electron microscopy (TEM)

A TEM works like a slide projector. The electron beam is the light beam. The electrons pass through the thinned materials (slide) and the output (image) is modulated by the structure (opaqueness) of the materials. The intensity of the transmitted electron beam varies with the sample structure. The transmitted image is magnified and projected onto the viewing screen. The resolving power is defined by $d = \lambda/n\sin\alpha$, and since the wavelength of electron beam is much less than that of the visible light (wavelength of green light is 500 nm versus $\lambda = 0.004$ nm for 100 keV electron) and there is very little electron deflection through a thin specimen, much higher resolution (atomic scale) than that achievable by optical microscopy and even conventional scanning electron microscopy can be obtained. With respect to the characterization of amorphous carbon and nanocrystalline carbon films, three kinds of TEM imaging techniques are usually used.

3.3.1. Electron diffraction (ED)

When the atomic plane space satisfies Bragg’s Law ($d = n\lambda/2\sin\theta$) and some other conditions, the electron diffraction pattern can be obtained. The simplest application is to identify crystalline substances based on the spacing of atomic planes within their structures. More detailed analysis of the ED patterns can provide important information on the orientation relationship between crystalline phases (such as coatings on substrates, precipitates in materials, etc.), the nature of defects in solids, order-disorder effects, and crystallite size analysis.

3.3.2. Dark field (DF) imaging

The technique utilizes a single diffracted beam to form the image in a TEM. This causes all regions of the specimen not of the same crystal structure and orientation in the region that produces the diffracted beam to appear dark in the final image. The method allows visual phase differentiation in the TEM.

3.3.3. Bright field (BF) imaging

It is a imaging mode in a TEM that uses only unscattered electrons to form the image. Contrast in such an
from amorphous carbon films do not convey much structural information either in the DF or BF mode, just like that of other amorphous materials. The DF patterns show a dark blurred ring without a bright spot. TEM images acquired from amorphous carbon films do not convey much structural information, but it is a powerful tool to judge whether the film is amorphous, i.e. whether the carbon atoms have enough short distance order or whether its ED pattern manifests as a diffuse intensity ring [145,151].

Though TEM images do not reveal much information about amorphous carbon films, it is very useful to assess nanocrystalline film structures. It can be used to determine the nanocrystalline size, structure, distribution [152-154].

Electron energy loss spectroscopy (EELS) is a very powerful way to reveal the detailed structures and have been used largely to research amorphous and nanocrystalline carbon films [36,47,158–163]. When an electron beam interacts with a film, it can give up all or part of its energy in the process. The energy loss corresponds to the film electron arrangement from 0 eV to 40 eV [47,59,161,158].

EELS can be classified as transmission EELS which is usually conducted in a transmission electron microscope (TEM) environment and is usually referred to by the acronym EELS using serial spectrometer or parallel EELS (PEELS) using parallel spectrometer, and surface EELS which is solely concerned with the interaction of an electron beam with a surface of a material and usually has the acronym CEELS (core-electron energy loss spectroscopy), ELS (electron energy loss spectroscopy), or HREELS (high resolution electron energy loss spectroscopy) [164,44,165]. Because the primary electron energy in HREELS is typically 2–5 eV, its energy is so low that it is usually used only for the analysis of molecules attached to the surface and the very shallow structural or vibrational message. It is therefore rarely used to unravel the details of carbon film structures [166–169].

A typical EELS spectrum can be divided into three separate regions:

- The zero-loss peak formed by the electrons of unscattered and elastically scattered electrons: in the analysis of the structural information of the carbon films, the width of the zero-loss signal can provide the resolution of the spectrometer [170].
- The low-loss region formed by the stimulated electronic transitions within the valence band of the solid, i.e. of only a few eV, and by stimulated collective oscillations of the electron sea of the solid: the energy loss usually extends to several tens of eV and for carbon films, it usually ranges from 0 eV to 40 eV [47,59,161,158].
- Higher energy losses resulting from electron energy losses due to the ionization under the interaction between the primary electrons and the inner shell electrons: the higher energy loss distribution usually has a long tail stretching to zero energy. For carbon films, the K edge is usually at 285 eV and above.

EELS has been shown to be a very useful tool in the unambiguous identification of diamond and graphite [162,140,171]. For diamond in the higher energy loss region, only the K edge peak at around 290 eV due to the excitation of the π* states of sp^3 appears, but the peak at 285 eV due to excitation to the π states cannot be observed. Both the 285 eV and 290 eV peaks will appear in graphite EELS. The latter peak is due to the π* states of sp^2. It can be postulated that in amorphous carbon films or in the nanocrystalline carbon films, the 285 eV peak and 290 eV peak will appear because the film structures are usually composed of either sp^3 or sp^2. Typical carbon K edge electron energy loss spectra acquired from different kinds of carbon films are shown in Fig. 11 [47,172].

Aside from the qualitative characterization of the amorphous carbon film structures, the high loss region in the carbon film EELS spectrum is usually used to yield quantitative information of the sp^3 and sp^2 contents. The most widely used quantitative sp^3 and sp^2 analysis method is proposed by Berger et al. [9]. In this method, graphite is used as a 100% sp^3 standard reference in the form of combined test specimen for electron microscopy. In the 100% sp^2 graphite, the ratio of the integrals under the 285 eV and 290 eV peaks is kept the same (1:3). For diamond (100% sp^3), the 285 eV peak does not appear at all. By considering that the intensity of the π* the feature is taken to be directly proportional to the number of π-bonded electrons in the material, the sp^3 content can be calculated.
fraction is calculated as follows:

\[
x = \frac{I_{\pi}/I_{\pi+\sigma}}{I_{\pi}/I_{\pi+\sigma}}_{\text{film}} - \frac{I_{\pi}/I_{\pi+\sigma}}{I_{\pi}/I_{\pi+\sigma}}_{\text{reference}} \tag{7}
\]

where \(I_{\pi}\) and \(I_{\pi+\sigma}\) are the integrated intensity of the \(\pi^*\) and \(\pi^* + \sigma^*\) features, respectively, and the subscripts “film” and “reference” refer to the ratio determined from the film and the 100% sp\(^2\) reference.

The graphite crystalline reference will result in an orientation dependence side effect, and to eliminate it, Alexandrou et al. have proposed to use C\(_60\) as a reference to eliminate the orientation problem completely [21,173]. By using the known 1:3 ratio of \(\pi^*\) to \(\sigma^*\) bonds for 100% sp\(^2\) and 0:4 ratio of \(\pi^*\) to \(\sigma^*\) bonds for 100% sp\(^3\), Cuomo et al. [160] have proposed another formula to calculate the atomic fraction of sp\(^2\) bonded carbon:

\[
x = \frac{3I_{\pi}/I_{\pi+\sigma}}{I_{\pi}/I_{\pi+\sigma}}_{\text{film}} - \frac{I_{\pi}/I_{\pi+\sigma}}{I_{\pi}/I_{\pi+\sigma}}_{\text{reference}} \tag{8}
\]

where \(I_{\pi}\) and \(I_{\pi+\sigma}\) are the integrated intensity in the range between 284 eV and 289 eV and from 290 eV to 305 eV, respectively.

Using K edge EELS to calculate the sp\(^2\) fraction, the selection of the proper energy windows (the integration boundary) needs particular attention. Berger et al. [9] have shown that the sp\(^2\) fraction reaches a stable value for an energy window greater than \(\sim 50\) eV. In addition, Robertson has proposed the following points [47]:

1. the films thickness should be appropriate;
2. the \(\pi^*\) peak in graphite is excitonically enhanced compared to the simple \(\pi^*\) peak in the conduction band DOS;
3. the reference sample should be randomly oriented microcrystalline graphite because the \(\pi^*\) peak is highly polarized [174];
4. additional peaks between 285 eV and 290 eV may appear in hydrocarbon films and fullerenes [175–179].

By assuming that the carbon film is composed entirely of sp\(^2\) and sp\(^3\) carbon and considering \(N_{e}/N_{o}\), the ratio of the number of \(\pi\) and \(\sigma\) orbitals for 100% sp\(^2\) and 100% sp\(^3\) bonded carbon, the number fraction of sp\(^2\) bonded atoms \((F_{\pi})\) is given by Pappas et al. [34] as follows:

\[
F_{\pi} = \frac{1 - 3N_{e}/N_{o}}{1 + N_{e}/N_{o}} \tag{9}
\]

The integrated boundaries for \(I_{\pi}\) and \(I_{\sigma}\) are from 284 eV to 289 eV and 290 eV to 305 eV.

The low energy loss region is usually from 0 eV to 40 eV (there is usually a peak at 63 ± 2 eV due to double loss to bulk plasmons), and the shifts in the position of the loss peak associated with the collective excitation modes of the valence electrons can be correlated to the change in the electron density [64]. Graphite displays a peak at 27.0 ± 0.5 eV attributable to \((\sigma + \pi)\) electron excitations while the peak at about 6–8 eV is due to \(\pi\) electron excitations [158,180]. The low energy loss region of diamond has been studied in details by Armon and Sellchop [181], Lurie and Wilson [140], Roberts and Walker [182], Himpsel et al. [183], and others. The typical low energy loss spectra are shown in Fig. 12 and the possible meaning of the peaks is given in Table 3.

The plasmon oscillations of the valence electrons reveal a broad peak in the low energy EELS spectra, and this has been used to evaluate the mass density of the carbon films and the sp\(^3\) fraction in the carbon films [173]. It should be noted that the peak position of the bulk plasmon mode in low-energy electron energy loss spectroscopy may vary with the substrate type, even if film deposition is carried out at the same temperature [160].

4. Surface morphology

4.1. Atomic force microscopy (AFM)

Scanning probe microscopy (SPM) is a powerful technique for the accurate measurement of surface morphology and properties. Two of the more common SPM techniques are atomic force microscopy (AFM) and scanning
Table 3

Low electron energy loss peaks of diamond (type-IIa single-crystal diamond)

<table>
<thead>
<tr>
<th>Elastic Peak</th>
<th>Peak Energy Loss (eV)</th>
<th>Relative Intensities</th>
</tr>
</thead>
<tbody>
<tr>
<td>$P_1$</td>
<td>$0.0 \pm 1.0$</td>
<td>75</td>
</tr>
<tr>
<td>$P_2$</td>
<td>$6.5 \pm 1.0$</td>
<td>0.71</td>
</tr>
<tr>
<td>$P_3$</td>
<td>$12.5 \pm 0.5$</td>
<td>0.93</td>
</tr>
<tr>
<td>$P_4$</td>
<td>$16.9 \pm 0.8$</td>
<td>0.43</td>
</tr>
<tr>
<td>$P_5$</td>
<td>$22.7 \pm 0.8$</td>
<td>1.36</td>
</tr>
<tr>
<td>$P_6$</td>
<td>$34.0 \pm 0.5$</td>
<td>1.05</td>
</tr>
<tr>
<td>$P_7$</td>
<td>$63.0 \pm 2.0$</td>
<td>0.05</td>
</tr>
</tbody>
</table>

Connotation:

- Elastic peak $\Gamma'_{25} \rightarrow \Gamma'_{15}$ can be assigned to several electronic transitions between crystalline levels: $\Sigma_2 \rightarrow \Sigma_3$, $L'_3 \rightarrow L_3$, $X_4 \rightarrow X_1$, $L'_3 \rightarrow L_1$, $\Gamma'_{25} \rightarrow \Gamma'_{1}$ or $X'_1 \rightarrow X'_1$ and/or loss to surface plasmons or contamination.
- Loss to Bulk plasmons.
- Double loss to bulk plasmons.

* Assume that the intensity of $P_0$ is 1 and the relative intensity is only given as a reference data. It will vary with different measurement situations.

* $P_3$ is still not well understood. It has been attributed to surface plasmons, interband transition, or contamination [161].

---

Fig. 12. Typical low energy loss spectra acquired from various carbon films.

Tunneling microscopy (STM) is a three-dimensional surface topography imaging technique, whereas STM provides pictures of atoms on surfaces. STM and AFM provide sub-nanometer resolution in all three dimensions, but because a voltage is exerted onto the sample, the technique is limited to conducting and semiconducting samples. AFM is more widely used in many applications, including thin films, nanocrystalline carbons, and amorphous carbon and nanocrystalline carbonsfilms, the application is quite straightforward. AFM study of carbon films is an attractive or repulsive force between the probe tip and the sample. As the tip is rastered over the sample, the forces are recorded and displayed to produce an AFM image. AFM measures the local attractive or repulsive forces between the probe tip and sample (AFM). A force detector is used to sense the sample. When the tip is rastered over the sample, the forces are recorded and displayed to produce an AFM image. AFM can achieve a resolution of 0.01 nm, and unlike electron microscopes, can image samples in air or liquids. AFM is used in many applications, including thin films, nanocrystalline carbons, and amorphous carbon and nanocrystalline carbons. The technique is quite straightforward. AFM study of carbon films is an attractive or repulsive force between the probe tip and the sample. As the tip is rastered over the sample, the forces are recorded and displayed to produce an AFM image. AFM measures the local attractive or repulsive forces between the probe tip and sample (AFM). A force detector is used to sense the sample. When the tip is rastered over the sample, the forces are recorded and displayed to produce an AFM image.
ogy and the deposition parameters can be readily determined [186–188].

Besides morphological observation and surface roughness calculation [189], AFM is also an excellent tool to investigate the nucleation and growth mechanism of amorphous carbon films [190,191]. By comparing the small difference revealed by the AFM images displayed in Fig. 13 and considering the different film growth phenomena observed for diamond like carbon films fabricated by vacuum arc deposition (VAD) and plasma immersion ion implantation-deposition (PIII-D), Li et al. have adopted a statistical formation theory to elucidate the possible nucleation and growth mechanisms [190].

4.2. Scanning electron microscopy (SEM)

Scanning electron microscopy (SEM) is perhaps the most widely used analytical technique. The basic components in a scanning electron microscope are depicted in Fig. 14 [192]. In an SEM instrument, a voltage is applied to an electron emitting filament typically made of W or LaB6, to produce an electron beam. The electrons are collimated and focused
Fig. 14. Schematic diagram showing the basic components of the SEM by electron optics including condenser lenses and objective lenses and eventually rastered by a set of scanning coils onto the sample surface. The electrons interact with the top few nanometers to several microns of the sample. Secondary electrons are emitted from the sample surface carrying information of the surface topography and they are then detected, amplified, processed, displayed, and stored.

SEM can be used to assess the surface morphology of amorphous carbon films and nanocrystalline carbon films [157,193–195]. However, because amorphous carbon films usually display a smooth morphology, especially when a semiconductor wafer is used as the substrate, SEM does not convey much detail about the film structure. Moreover, because the electrical conductance of amorphous carbon films is often low, surface charging can occur and distort the resulting SEM image. In general, SEM is used in the following situations:

1. SEM can be used to determine nano-structured compounds or particles formed on the amorphous carbon film surface or film delamination due to mismatch of the film and substrate. An example is shown in Fig. 15(a) [193,194,196–199].
2. The surface morphology of amorphous and nanocrystalline carbon films can be monitored, especially for the latter ones and an example is illustrated in Fig. 15(b) [153,200–203].
3. It can be used to observe the cross section of a film to determine the film thickness, to deduce the film growth rate, or to investigate the growth mechanism. It is also proper to observe the cross section of multi-layered films and an example is displayed in Fig. 15(c) [157,204,205].
4. It is an excellent tool to observe the friction tracks and analyze the debris after a friction test on the amorphous film.

Fig. 15. SEM images of various carbon films to demonstrate the versatility of SEM: (a) RF plasma assisted pulsed laser deposited carbon films [197]; (b) nano-diamond films deposited by direct current glow discharge assisted chemical vapor deposition [153]; (c) 1.5 μm DLC film deposited at 60° ion incidence [205]; (d) corrosion spots on a disk after corrosion tests [206].
or nanocrystalline carbon films. It is thus suitable to assess the results of mechanical or chemical treatment. An example is shown in Fig. 15 (d) [157,206,207].

5. Nuclear magnetic resonance

Many isotopes such as $^{13}$C and $^1$H possess nuclear spin or angular momentum. Since a spinning charge generates a magnetic field, and the angular momentum results in a magnetic moment. When placed in a magnetic field $B_0$, the spinning nuclei do not all align with their magnetic moments in the field direction. By applying a radio-frequency field of an appropriate frequency orthogonal to $B_0$, the nuclear spins will experience resonance and become aligned. At this resonance frequency, the nuclear magnetic dipoles in the lower energy state flip over and by detecting the flipping, structural information can be gained by the technique of nuclear magnetic resonance (NMR) spectroscopy [208].

It is generally accepted that NMR yields quantitative results of the $sp^3/sp^2$ ratio in amorphous and nanocrystalline carbon films [209,210]. In fact, it has been used as a standard method to calibrate the $sp^2/sp^3$ ratio derived from other methods [211]. In the $sp^2/sp^3$ ratio measurement, the $sp^2$ and $sp^3$ carbon NMR spectra show two separate peaks at different chemical shift positions. The $sp^2$ and $sp^3$ peak chemical shifts vary slightly in different types of amorphous carbon films. Some of the $sp^2$ and $sp^3$ NMR peak positions of the carbon films are summarized in Table 4.

NMR is thus a relatively simple and powerful method to determine the $sp^3/sp^2$ ratio because each nucleus gives rise to the same integrated NMR signal intensity regardless of its chemical environment. A typical NMR spectrum is displayed in Fig. 16. The $sp^2$ and $sp^3$ atoms show two separate peaks, especially in cross polarization magic angle spinning (CPMAS) NMR spectra, and the ratio of $sp^2$ to $sp^3$ is equal to the peak integrated radio. By combining the results from $^{13}$C NMR and $^1$H NMR, the hydrogen content as well as detailed C–H bonding information can be obtained [216].

The limitation of NMR is that the natural abundance of $^{13}$C is relatively low (about 1.1%) [220], and a large amount

<table>
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<tr>
<td>Examples of peak positions of $sp^2$ and $sp^3$ in NMR spectra acquired from carbon films</td>
</tr>
<tr>
<td><strong>Film types</strong></td>
</tr>
<tr>
<td>Nature diamond powder</td>
</tr>
<tr>
<td>Graphite</td>
</tr>
<tr>
<td>DLC</td>
</tr>
<tr>
<td>a-C:H</td>
</tr>
<tr>
<td>a-C:H</td>
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<tr>
<td>a-C:H</td>
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<tr>
<td>a-C</td>
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<tr>
<td>a-C:H</td>
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</tbody>
</table>
of materials (typically more than 30 mg) is needed for the analysis [211]. Although the technique is simple and informative, it is not a very common practice and the researchers must be aware of the following ambiguities and precautions:

- In two cases, particular carbon atoms may be undetected. Firstly, the lifetime of carbon atoms near unpaired electrons may be broadened beyond detectability, and secondly, carbons present in hydrogen deficient structures may be difficult to detect due to excessively long cross polarization and spin-lattice relaxation times. However, this does not affect the derivation of the sp2/sp3 ratio because the detected 13C atoms distribute in the whole film evenly [219].
- The presence of hydrogen in the sample is required to allow efficient use of cross-polarization techniques [211].
- When acquiring the NMR spectrum from carbon films, the time should be long enough to allow all the spin-lattice relaxation signals to be fully detected.
- For the strained carbon bonding in tetrahedral amorphous carbon films, except the sp2 peak at 140 ppm and the sp3 peak at 39 ppm, an additional peak at 66 ppm (related to TMS) corresponds to compressed graphitic C [220].

6. X-ray reflectivity

X-ray reflectivity (XRR) is a nondestructive method to examine the amorphous carbon film density, thickness, and microscopy roughness [223–227]. In this technique, the X-ray reflectivity is measured while varying the X-ray incident angle θ from a low value (e.g. at a glancing angle of ~0.1°) to a higher value (e.g. 3°). During the incident angle increase, the recorded reflectivity intensity gradually increases due to the sin(θ) dependence of the incident intensity. After a critical angle, θc, has been reached, the detected reflectivity will decrease rapidly. The reflection of X-rays from a layered, dielectric medium was discussed by Parratt who derived a recursion formula to calculate the reflected intensity from successive interfaces [228]. The X-ray reflectivity is determined by the density as well as surface and interface roughness of the films, and in turn, these films properties can contribute to the reflectivity: the air–film interface and the carbon/substrate interfaces and so the period of this oscillation is directly related to the thickness of the carbon film [230,231]. For a thin film on a substrate, there will be two contributions to the reflectivity: the air–film interface and the film–substrate interface. Considering that real interfaces have some roughness and there is a gradual change in the electron density, the X-ray reflected from the two interfaces interferes and the reflectivity is approximately given by [223,232]:

\[
R = \frac{r_0 + r_1 \exp(iQt)}{1 + r_0 r_1 \exp(-iQT)}
\]  

\text{(14)}

where \(N_A\) is the Avogadro number, \(\mu\) the linear absorption coefficient, \(\rho^0\) the classical electron radius, \(f^0\) and \(f^\prime\) are the dispersion and absorptive corrections, and at a given \(\lambda\), \(f^0\) and \(f^\prime\) can be calculated for different atoms [226]. Applying Snell’s law at the air/film interface, the critical angle can be derived:

\[
\theta_c = \frac{\sqrt{2}}{\lambda} \sum_{j} \frac{\rho_j}{Z_j + f^\prime_j} (\frac{M_j}{\rho_j})^{1/2}
\]  

\text{(13)}

Using the above formula, the film density can be obtained. An accurate measurement of the density of carbon films is important, since this relates to the presence of microvoids, the molecular structure of the film, and how the carbon atoms are bonded to each other [223].

The modulation in the reflectivity arises from the interference between X-rays scattered from the carbon/air and the carbon/substrate interfaces and so the period of this oscillation is directly related to the thickness of the carbon film [230,231]. For a thin film on a substrate, there will be two contributions to the reflectivity: the air–film interface and the film–substrate interface. Considering that real interfaces have some roughness and there is a gradual change in the electron density, the X-ray reflected from the two interfaces interferes and the reflectivity is approximately given by [223,232]:

\[
\frac{1}{10^6}
\]  

\text{Fig. 17. Typical X-ray reflectivity from amorphous carbon films.}
Carbon, together with hydrogen, perhaps is the most magical element in the world. They are the backbone of the organic materials and many inorganic materials. Carbon atoms form intermolecular C–C and C–H bond arrangements and orders in a three-dimensional network to make the structure of carbon-containing films very complex. The structural characterization methods described in this paper are the most frequently used ones. It should be borne in mind that the information gained from the amorphous carbon films is usually "statistical" in nature since at the present, we still lack a direct atomic characterization method that can be used over a large scale. In addition, because of the complex structure of carbon films, inner stress, dangling bonds, and dislocations, characterization of the carbon film structure may not be definite. In most cases, the use of multiple techniques to tackle the problem from several perspectives is recommended, especially when it is the first time to analyze a "new" carbon film.

Several techniques are not discussed here due to the length of the article. For example, mechanical characterization methods such as nano indenter hardness can also convey very important messages. Other notable ones include X-ray, neutron and electrons diffraction, ellipsometry, elastic recoil detection, and readers are suggested to peruse other textbooks and papers or articles cited in this paper.

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where $r_s$ and $r_i$ are the reflection amplitudes (including roughness) at the surface (air-film) and the inner interface (film-substrate), respectively, $t$ is the film thickness, and $Q (4\pi n \sin \theta)$ is the scattering vector. Using this relationship, the reflectivity intensity decay and the fringes above $r_i$ can be fitted [223], and the surface thickness and the surface roughness (two interface) can subsequently be derived [4,223,225,226].


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